2SC4262

Silicon NPN Epitaxial

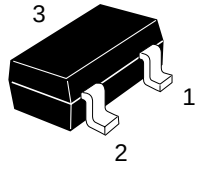
HITACHI

Application

UHF / VHF Local oscillator

Outline

CMPAK



1. Emitter
2. Base
3. Collector

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Absolute Maximum Ratings (Ta = 25°C)

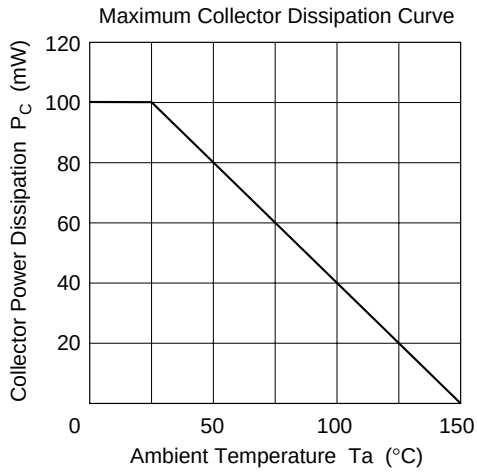
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	15	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

Electrical Characteristics (Ta = 25°C)

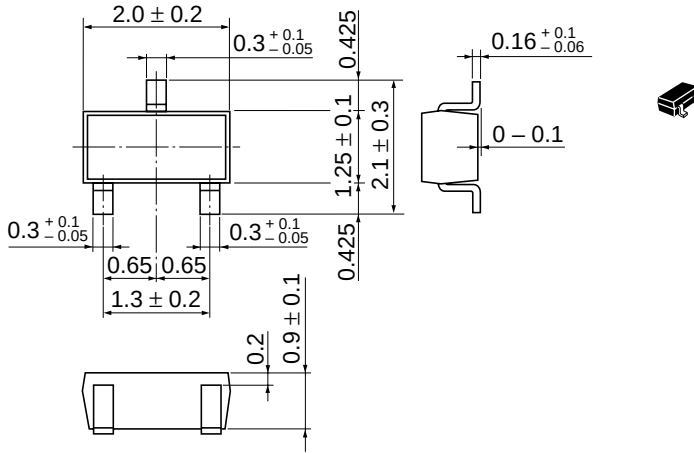
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	20	—	—	V	I_C = 10 µA, I_E = 0
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	15	—	—	V	I_C = 1 mA, R_{BE} = ∞
Collector cutoff current	I_{CBO}	—	—	0.5	µA	V_{CB} = 15 V, I_E = 0
Emitter cutoff current	I_{EBO}	—	—	1.0	µA	V_{EB} = 3 V, I_C = 0
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	I_C = 20 mA, I_B = 4 mA
DC current transfer ratio	h_{FE}	50	—	200		V_{CE} = 10 V, I_C = 5 mA
Collector output capacitance	Cob	—	—	1.0	pF	V_{CB} = 10 V, I_E = 0, f = 1MHz
Gain bandwidth product	f_T	1.4	2.9	—	GHz	V_{CE} = 10 V, I_C = 5 mA

Note: Marking is “IP–”.

See characteristic curves of 2SC3793.


Maximum Collector Dissipation Curve
Collector Power Dissipation P_C (mW)
120
100
80
60
40
20
0
50
100
150
Ambient Temperature Ta (°C)

Unit: mm



Hitachi Code	CMPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.006 g

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